L Number	Hits	Search Text	DB	Time stamp
1	444	(shallow adj junction) and (deep adj	USPAT;	2004/10/25
2		junction)	US-PGPUB;	09:43
		, junction,	EPO; JPO;	09:43
	:		DERWENT;	
			IBM_TDB	
	180	(shallow adi impetian) with (door adi	_	2004/40/25
	180	(shallow adj junction) with (deep adj junction)	USPAT;	2004/10/25
		junction	US-PGPUB;	09:43
			EPO; JPO;	
			DERWENT;	
	4-7	(fals all and a 41 form all and a 44 form a 41 form	IBM_TDB	0004/40/05
3	17	((shallow adj junction) with (deep adj	USPAT;	2004/10/25
		junction)).clm.	US-PGPUB;	09:44
			EPO; JPO;	
			DERWENT;	
_			IBM_TDB	
4	0	((shallow adj junction) with (deep adj	USPAT;	2004/10/25
		junction)).clm. and (laser near (anneal or	US-PGPUB;	09:45
		annealing or annealed)).clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
5	1	((shallow adj junction) with (deep adj	USPAT;	2004/10/25
		junction)).clm. and (laser near (anneal or	US-PGPUB;	09:45
		annealing or annealed))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
6	1	((shallow adj junction) with (deep adj	USPAT;	2004/10/25
		junction)).clm. and (amorphize or	US-PGPUB;	09:46
		amorphizing or amorphized or	EPO; JPO;	
		amorphization).clm.	DERWENT;	
			IBM_TDB	
7	1	((shallow adj junction) and (deep adj	USPAT;	2004/10/25
		junction)).clm. and (amorphize or	US-PGPUB;	09:46
		amorphizing or amorphized or	EPO; JPO;	
		amorphization).clm.	DERWENT;	
			IBM_TDB	
8	1	((shallow adj junction) and (deep adj	USPAT;	2004/10/25
		junction)).ti,ab,clm. and (amorphize or	US-PGPUB;	09:46
		amorphizing or amorphized or	EPO; JPO;	
		amorphization).clm.	DERWENT;	
			IBM_TDB	
9	1	((shallow adj junction) and (deep adj	USPAT;	2004/10/25
		junction)).ti,ab,clm. and (amorphize or	US-PGPUB;	09:46
		amorphizing or amorphized or	EPO; JPO;	
		amorphization).ti,ab,clm.	DERWENT;	
		_ , , ,	IBM_TDB	
10	2	((shallow adj junction) and (deep adj	USPAT;	2004/10/25
	i	junction)).ti,ab,clm. and (amorphize or	US-PGPUB;	09:47
		amorphizing or amorphized or	EPO; JPO;	-
		amorphization)	DERWENT;	
			IBM_TDB	

			ų	
11	25	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation)).clm.	US-PGPUB;	09:48
			EPO; JPO;	
	1		DERWENT;	
4.0			IBM_TDB	
12	10	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:48
		same source same drain).clm.	EPO; JPO;	
			DERWENT;	
40		/!	IBM_TDB	0004/40/05
13	1	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate same source same drain same	US-PGPUB;	09:48
			EPO; JPO;	
		capacitance).clm.	DERWENT;	
14	1	/lunction come (omembine or omembine	IBM_TDB	2004/10/25
14		(junction same (amorphize or amorphizing or amorphized or amorphiation) same gate	USPAT;	2004/10/25 09:48
		same source same drain same capacitance)	US-PGPUB;	U3:40
	,	, same source same urain same capacitance).	EPO; JPO; DERWENT;	
			IBM_TDB	
15	23	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
"	23	or amorphized or amorphiation) same gate	US-PGPUB;	09:48
		same source same drain).ti,ab,clm.	EPO; JPO;	03.40
		· ·	DERWENT;	
			IBM_TDB	
16	6	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:49
		same source same drain).ti,ab,clm. and	EPO; JPO;	33.73
ŀ		capacitance	DERWENT;	
			IBM_TDB	
17	3	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:50
		same source same drain).ti,ab,clm. and	EPO; JPO;	
		capacitance and laser	DERWENT;	
		·	IBM_TDB	
18	3	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:51
		same source same drain).ti,ab,clm. and	EPO; JPO;	
		capacitance and laser and (ion adj (implant	DERWENT;	
	1 I	or implanting or implanted or implantation))	IBM_TDB	
19	2	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:52
		same source same drain).ti,ab,clm. and	EPO; JPO;	
		capacitance and laser and (ion adj (implant	DERWENT;	
		or implanting or implanted or implantation))	IBM_TDB	
	_	and ((shallow or deep) adj junction)		
20	2	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
		or amorphized or amorphiation) same gate	US-PGPUB;	09:52
		same source same drain).ti,ab,clm. and	EPO; JPO;	
		capacitance and laser and (ion adj (implant	DERWENT;	
		or implanting or implanted or implantation))	IBM_TDB	
		and ((shallow or deep) adj junction) and		·
		crystal		

21	2	(junction same (amorphize or amorphizing	USPAT;	2004/10/25
	_	or amorphized or amorphiation) same gate	US-PGPUB;	09:53
		same source same drain).ti,ab,clm. and	EPO; JPO;	
		capacitance and laser and (ion adj (implant	DERWENT;	
		or implanting or implanted or implantation))	IBM_TDB	
		and ((shallow or deep) adj junction) and		
		(single adj crystal)		
22	2	(junction and (amorphize or amorphizing or	USPAT;	2004/10/25
	_	amorphized or amorphiation) and gate and	US-PGPUB;	09:54
		source and drain).ti,ab,clm. and	EPO; JPO;	00.04
		capacitance and laser and (ion adj (implant	DERWENT;	
		or implanting or implanted or implantation))	IBM_TDB	
		and ((shallow or deep) adj junction) and	15111_155	
		(single adj crystal)		
23	16	(single auj crystar) (junction and (amorphize or amorphizing or	USPAT;	2004/10/25
	'9	amorphized or amorphiation) and gate and	US-PGPUB;	09:58
		source and drain) and capacitance and	EPO; JPO;	09.30
		laser and (ion adj (implant or implanting or	DERWENT;	
		implanted or implantation)) and ((shallow or	IBM_TDB	
		deep) adj junction) and (single adj crystal)	10111_100	
24	2	((junction and (amorphize or amorphizing or	USPAT;	2004/10/25
	_	amorphized or amorphiation) and gate and	US-PGPUB;	10:01
		source and drain) and capacitance and	EPO; JPO;	10:01
		laser and (ion adj (implant or implanting or	DERWENT;	
		implanted or implantation)) and ((shallow or	IBM_TDB	
		deep) adj junction) and (single adj crystal))	IDM_IDB	
		and (sharp adj (dopant or impurity) adj		
•	1	profile)		
25	4	((junction and (amorphize or amorphizing or	USPAT;	2004/10/25
	-	amorphized or amorphiation) and gate and	US-PGPUB;	10:04
		source and drain) and capacitance and	EPO; JPO;	10.04
		laser and (ion adj (implant or implanting or	DERWENT;	
		implanted or implantation)) and ((shallow or	IBM_TDB	
		deep) adj junction) and (single adj crystal))	10111_100	
		and ((amorphize or amorphized or		
		amorphizing or amorphization) near5		
		(dopant or impurity))		
26	1	((junction and (amorphize or amorphizing or	USPAT;	2004/10/25
	•	amorphized or amorphiation) and gate and	US-PGPUB;	10:04
	1	source and drain) and capacitance and	EPO; JPO;	10.04
		laser and (ion adj (implant or implanting or	DERWENT;	
		implanted or implantation)) and ((shallow or	IBM_TDB	
		deep) adj junction) and (single adj crystal))		
		and ((amorphize or amorphized or		
		amorphizing or amorphization) near5		
		(dopant or impurity) near5 junction)		
	<u></u>	The state of the s	I	L